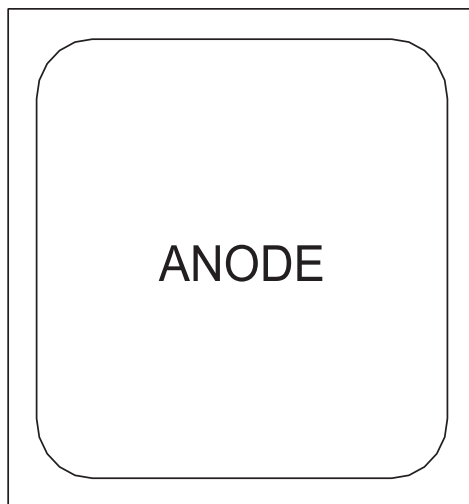


**PROCESS DETAILS**

Process	GLASS PASSIVATED MESA
Die Size	25 x 25 MILS
Die Thickness	9.5 MILS
Anode Bonding Pad Area	14.5 x 14.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

**GEOMETRY**



BACKSIDE CATHODE R0

**GROSS DIE PER 4 INCH WAFER**

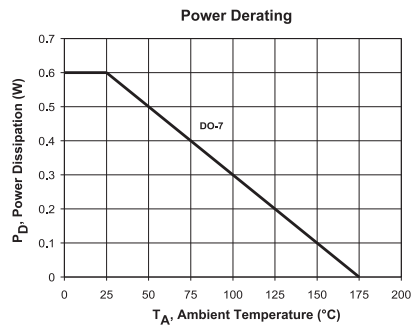
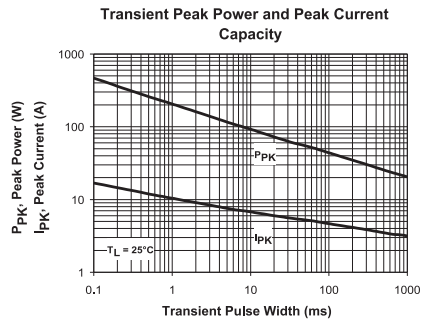
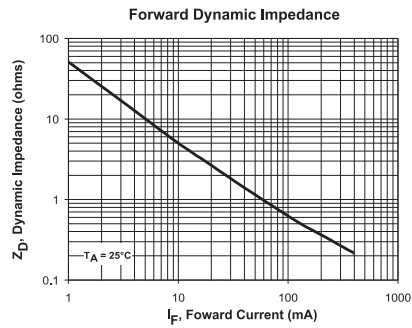
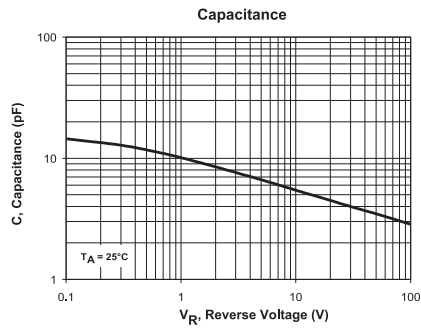
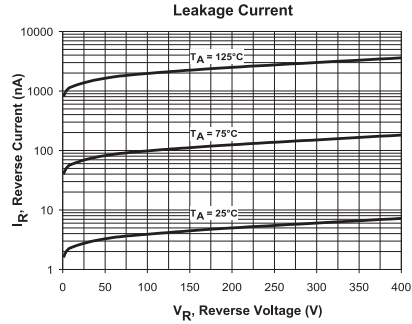
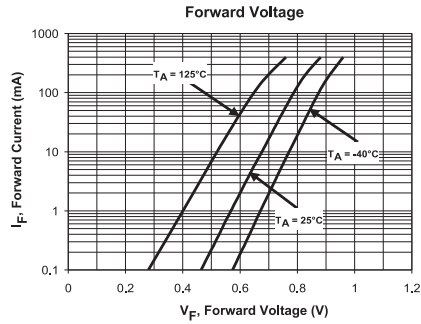
18,080

**PRINCIPAL DEVICE TYPES**

1N645 thru 1N649  
CBRHD-02 Series

145 Adams Avenue  
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R2 (16- September 2003)



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